

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-24. (Canceled)

25. (Currently Amended) ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 23, comprising:~~

producing a first semiconductor wafer including first semiconductor chips;

producing a second semiconductor wafer including second semiconductor chips;

performing burn-in of the first and the second semiconductor wafer;

cutting the first and second semiconductor wafers to produce a batch of first semiconductor chips and a batch of second semiconductor chips, respectively,
and

assembling one of the first semiconductor chips and one of the second semiconductor chips to produce the semiconductor device,

wherein assembling includes a process of forming a stacked arrangement of one or more of the first semiconductor chips and one or more of the second semiconductor chips on a substrate to produce the semiconductor device and providing prescribed electrical connections therebetween.

26. (Currently Amended) ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 25, comprising:~~

producing a first semiconductor wafer including first semiconductor chips;

producing a second semiconductor wafer including second semiconductor chips;

performing burn-in of the first and the second semiconductor wafer;

cutting the first and second semiconductor wafers to produce a batch of first semiconductor chips and a batch of second semiconductor chips, respectively, and

assembling one of the first semiconductor chips and one of the second semiconductor chips to produce the semiconductor device,

wherein assembling includes a process of forming a stacked arrangement of one or more of the first semiconductor chips and one or more of the second semiconductor chips on a substrate to produce the semiconductor device and providing prescribed electrical connections therebetween, and

wherein the substrate is a wiring substrate.

27. (Currently Amended) ~~The~~ A method of manufacturing a semiconductor device ~~according to claim 23, comprising:~~

producing a first semiconductor wafer including first semiconductor chips;

producing a second semiconductor wafer including second semiconductor chips;

performing burn-in of the first and the second semiconductor wafer;

cutting the first and second semiconductor wafers to produce a batch of first semiconductor chips and a batch of second semiconductor chips, respectively, and

assembling one of the first semiconductor chips and one of the second semiconductor chips to produce the semiconductor device,

wherein assembling includes a process of forming a stacked arrangement of one or more of the first semiconductor chips and one or more of the second semiconductor chips on a substrate to produce the semiconductor device and providing prescribed electrical connections therebetween, and

wherein each of the first semiconductor chips includes a volatile memory and each of the second chips includes a nonvolatile memory.

28. (New) The method of manufacturing a semiconductor device according to claim 25,

wherein performance of the burn-in comprises:

performing a contact check for judging electric connection/non-connection between each needle connected to a test apparatus and each terminal provided in each of the first and second semiconductor chips of the first and second semiconductor wafers, and

wherein each of the first semiconductor chips includes a volatile memory and each of the second chips involves a nonvolatile memory.

29. (New) The method of manufacturing a semiconductor device according to claim 26,

wherein performance of the burn-in comprises:

performing a contact check for judging electric connection/non-connection between each needle connected to a test apparatus and each terminal provided in each of the first and second semiconductor chips of the first and second semiconductor wafers, and

wherein each of the first semiconductor chips includes a volatile memory and each of the second chips involves a nonvolatile memory.

30. (New) The method of manufacturing a semiconductor device according to claim 25,

wherein performance of the burn-in comprises:

performing a contact check for judging electric connection/non-connection between each needle connected to a test apparatus and each terminal provided in each of the first and second semiconductor chips of the first and second semiconductor wafers, and

wherein the substrate is a wiring substrate.